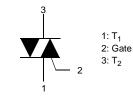


FKN08PN60S TRIAC (Silicon Bidirectional Thyristor)

Application Explanation

- Switching mode power supply, light dimmer, electric flasher unit, hair drier
- TV sets, stereo, refrigerator, washing machine
- Electric blanket, solenoid driver, small motor control
- Photo copier, electric tool





Absolute Maximum Ratings T_a = 25°C unless otherwise noted

Symbol	Parameter	Value		Rating	Units
V _{DRM} V _{RRM}	Peak Repetitive Off-State Voltage	Sine Wave 50 to 60Hz, Gate Open		600	V
I _{T (RMS)}	RMS On-State Current	Commercial frequency, sine full wave 360° conduction, Tc= 70 ℃		0.8	A
I _{TSM}	Surge On-State Current	Sinewave half cycle, peak value, non-repetitive	60Hz	8	A
l ² t	I ² t for Fusing	Value corresponding to halfwave, surge on-state current, tp=8.33ms	•	0.26	A ² s
P _{GM}	Peak Gate Power Dissipation			5	W
P _{G (AV)}	Average Gate Power Dissipation			0.1	W
V _{GM}	Peak Gate Voltage			5	V
I _{GM}	Peak Gate Current			1	А
TJ	Junction Temperature			- 40 ~ 125	°C
T _{STG}	Storage Temperature			- 40 ~ 125	°C

Thermal Characteristics

Symbol	Parameter	Value	Units
R_{\thetaJC}	Thermal Resistance, Junction to Case (note1)	45	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient (note2)	160	°C/W

Note1: Infinite cooling condition.

Note2: JESD51-10 (Test Borad: FR4 3.0"*4.5"*0.062", Minimum land pad)

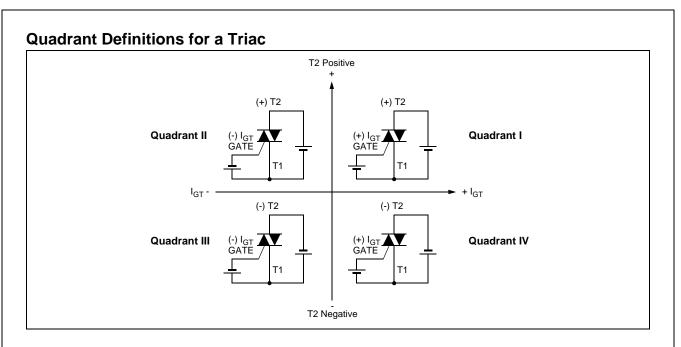
February 2008

Symbol	Parameter		Test Condition		Min.	Тур.	Max.	Units
I _{DRM} I _{RRM}	Repetieive Peak Off-State Current		V _{DRM} /V _{RRM} applied		-	-	100	μΑ
V _{TM}	On-State Voltage		T _C =25°C, I _{TM} =1.12A Instantaneous measurement		-	-	1.8	V
		Ι		T2(+), Gate (+)	-	-	2.0	V
V _{GT}	Gate Trigger Voltage ^(Note 2)	П	V_{D} =12V, R _L =100 Ω	T2(+), Gate (-)	-	-	2.0	V
				T2(-), Gate (-)	-	-	2.0	V
	Gate Trigger Current (Note 2)	Ι	V _D =12V, R _L =100Ω	T2(+), Gate (+)	-	-	5	mA
I _{GT}		П		T2(+), Gate (-)	-	-	5	mA
		III		T2(-), Gate (-)	-	-	5	mA
V _{GD}	Gate Non-Trigger Voltage		T _J =125°C, V _D =1/2V _{DRM}		0.2	-	-	V
I _H	Holding Current (I, II, III)		V _D = 12V, I _{TM} = 200mA		-	-	15	mA
ΙL	Latching Current	I, III	V _D = 12V, I _G = 10mA		-	-	15	mA
		П			-	-	20	mA
dv/dt(s)	Critical Rate of Rise of $V_{DRM} = 63\%$ Rated, $T_j = 125^{\circ}C$,Off-State VoltagExponential Rise		20	-	-	V/µs		
dv/dt(c)	Critical-Rate of Rise of Off-State Com- mutating Voltage (di/dt=-0.7A/uS)				3.0	-	-	V/µs

Electrical Characteristics T_c = 25°C unless otherwise noted

Commutation dv/dt test

V _{DRM} (V)	Test Condition	Commutating voltage and current waveforms (inductive load)
FKN08PN60S	 Junction Temperature T_J=125°C Rate of decay of on-state commutating current (di/dt)_C Peak off-state voltage V_D = 300V 	Supply Voltage Time Main Current Time Main Voltage Vp



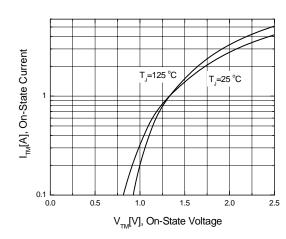
Package Marking and Ordering Information

Device Marking	Device	Package	Packing	Tape Width	Quantity
K08PN60S	FKN08PN60S	TO-92	BULK		

Typical Performance Characteristics

Figure 1. On-State Characteristics





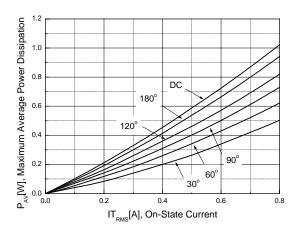


Figure 3. RMS Current Rating

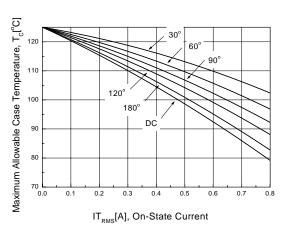


Figure5. Typical Gate Voltage vs Junction Temperarure

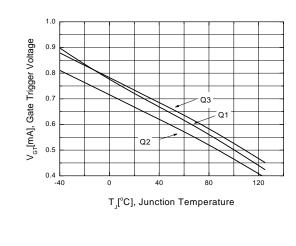
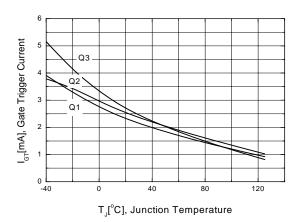
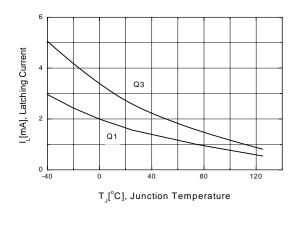


Figure 4. Typical Gate Trigger Current vs Junction Temperature

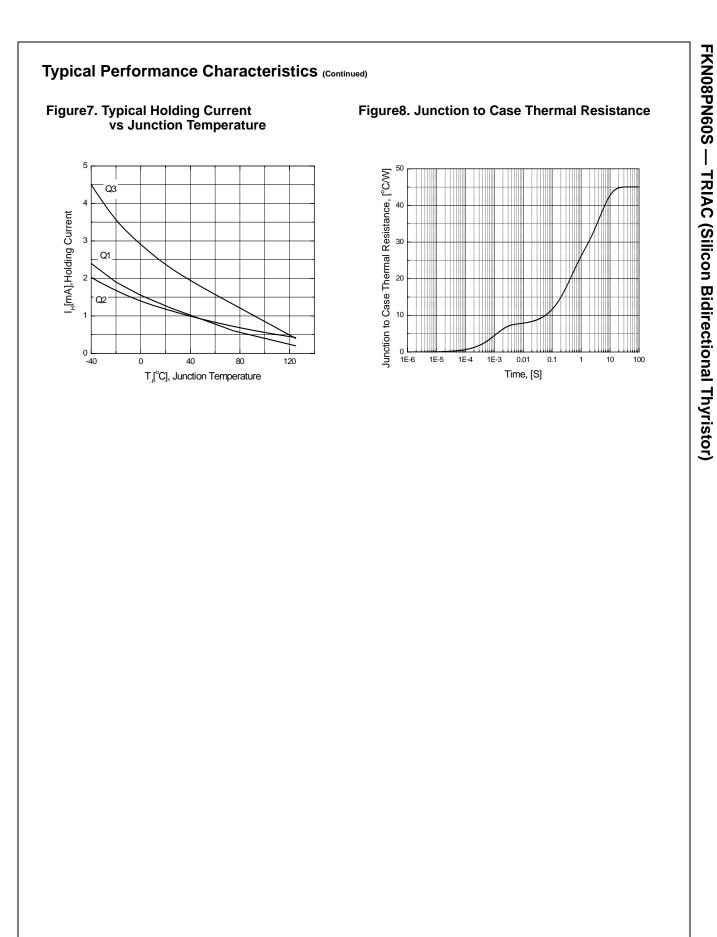


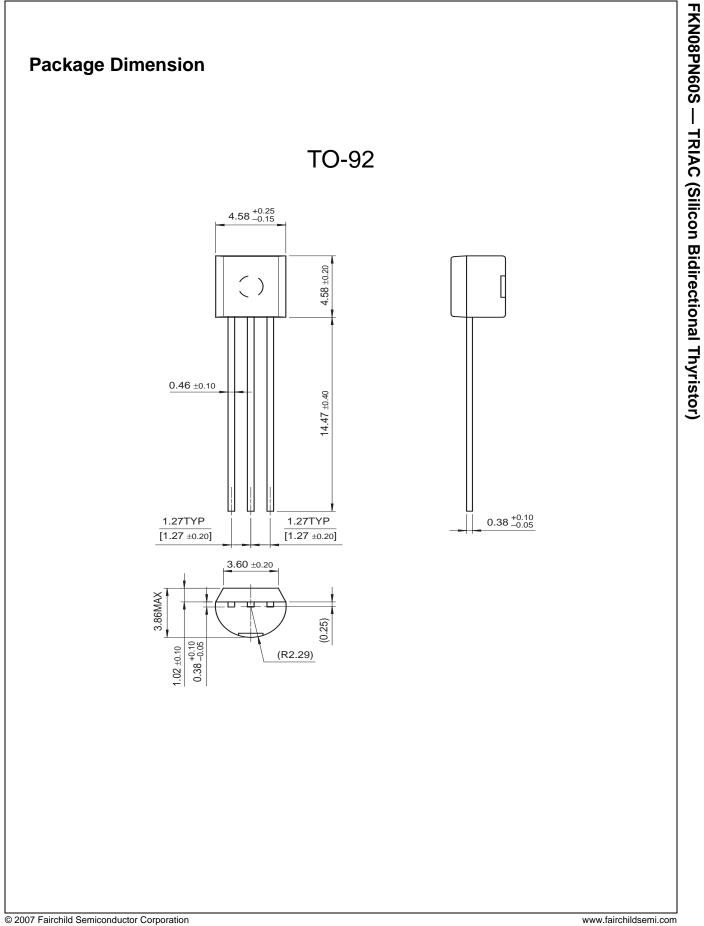




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